

SanDisk, Toshiba Unveil 256Gb BiCS Flash

Written by Marco Attard
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SanDisk and Toshiba announce the next generation of BiCS (Bit Cost Scaling) flash memory-- what the two companies claim is the first 256 gigabit (32GB) 48-layer BiCS 3D NAND flash using 3-bit-per-cell TLC (triple-level cell) technology.



BiCS flash uses a 48-layer stacking process to surpass the storage capacity of current 2D NAND flash while enhancing write/erase reliability, endurance and write speeds. Back in March Toshiba revealed an earlier version of the technology with 128 gigabit (16GB) 48-layer BiCS non-volatile memory chips.

The companies add the 256Gb device is suitable for diverse applications, including consumer SSDs, mobile devices, memory cards and enterprise data centre SSDs.

"From day one, Toshiba's strategy has been to extend our floating gate technology, which features the world's smallest 15nm 128Gb die," the company says. "Our announcement of BiCS flash, the industry's first 48-layer 3D technology, is very significant in that we are enabling a competitive, smooth migration to 3D flash memory-- to support the storage market's demand for ever-increasing densities."

Toshiba is readying BiCS flash mass production at its new Fab2 facility in Yokkaichi, Japan, with sample shipments to start from September 2015.

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